

9097250 TOSHIBA (DISCRETE/OPTO)

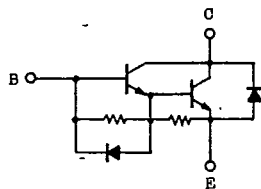
90D 16279 DT-33-35



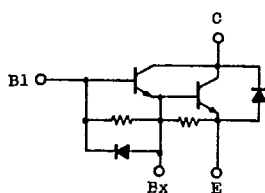
# SEMICONDUCTOR

## TECHNICAL DATA

MG200H1AL2  
MG200H1FL1A

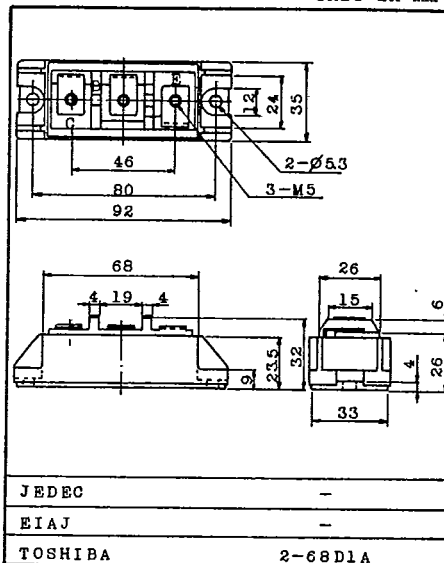


MG200H1AL2



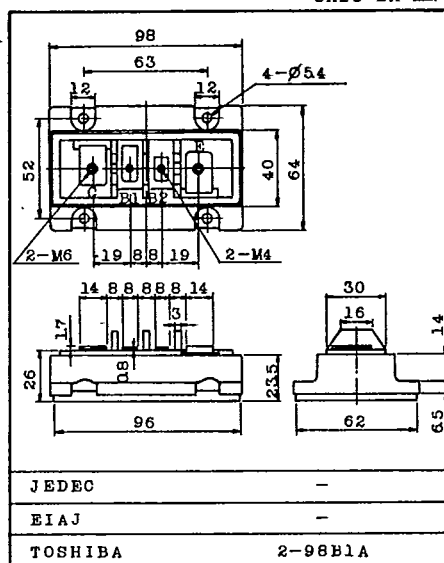
MG200H1FL1

Unit in mm



Weight : 210g

Unit in mm



Weight : 420g

TOSHIBA CORPORATION

GT1A2A

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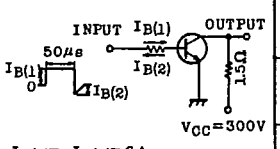
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MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		$V_{CB10}$	600	V
Collector-Emitter Voltage		$V_{CEO}$	600	V
Collector-Emitter Sustaining Voltage		$V_{CEO(SUS)}$	550	V
Emitter-Base Voltage		$V_{EB10}$	6	V
Collector Current	DC	$I_C$	200	A
	1ms	$I_C$	400	
	DC	$-I_C$	200	
Base Current		$I_{B1}$	8	A
Collector Power Dissipation ( $T_c=25^\circ\text{C}$ )		$P_C$	800	W
Junction Temperature		$T_j$	150	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	-40~125	$^\circ\text{C}$
Isolation Voltage		$V_{isol}$	2500 (AC 1 Minute)	V
Screw Torque (Terminal M4/M6/Mounting)		-	20/30/30	kg·cm

ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		$I_{CB10}$	$V_{CB1}=600\text{V}$ , $I_E=0$	-	-	2.0	mA
Emitter Cut-off Current		$I_{EB10}$	$V_{EB1}=6\text{V}$ , $I_C=0$	-	-	400	mA
Collector-Emitter Sustaining Voltage		$V_{CEO(SUS)}$	$I_C=0.5\text{A}$ , $L=40\text{mH}$	550	-	-	V
DC Current Gain		$h_{FE}$	$V_{CE}=5\text{V}$ , $I_C=200\text{A}$	80	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=200\text{A}$ , $I_{B1}=6\text{A}$	-	-	2.0	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$		-	-	2.7	V
Emitter-Collector Voltage		$V_{ECO}$	$I_E=200\text{A}$ , $I_{B1}=0$	-	-	1.5	V
Reverse Recovery Time		$t_{rr}$	$-I_C=200\text{A}$ , $V_{EB1}=3\text{V}$ $V_{CE}=300\text{V}$	-	-	2.0	$\mu\text{s}$
Collector Output Capacitance		$C_{ob1}$	$V_{CB1}=50\text{V}$ , $I_E=0$ $f=1\text{MHz}$	-	1670	-	pF
Switching Time	Turn-on Time	$t_{on}$		-	-	2.0	$\mu\text{s}$
	Storage Time	$t_{stg}$		-	-	12	
	Fall Time	$t_f$		-	-	4.0	
Thermal Resistance (Junction to Case)		$R_{th(j-c)}$	Transistor	-	-	0.156	$^\circ\text{C/W}$
			Diode	-	-	0.65	

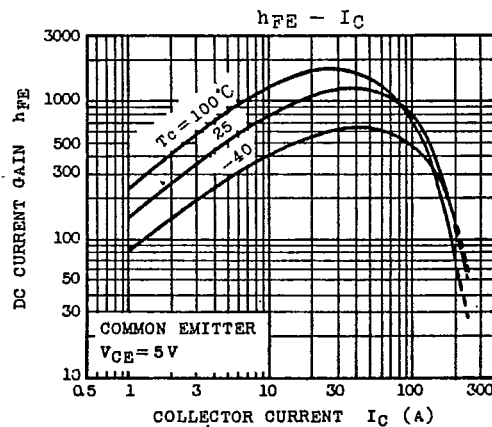
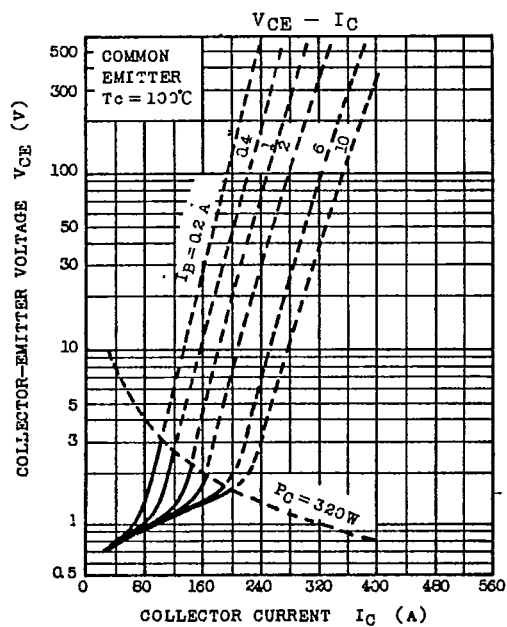
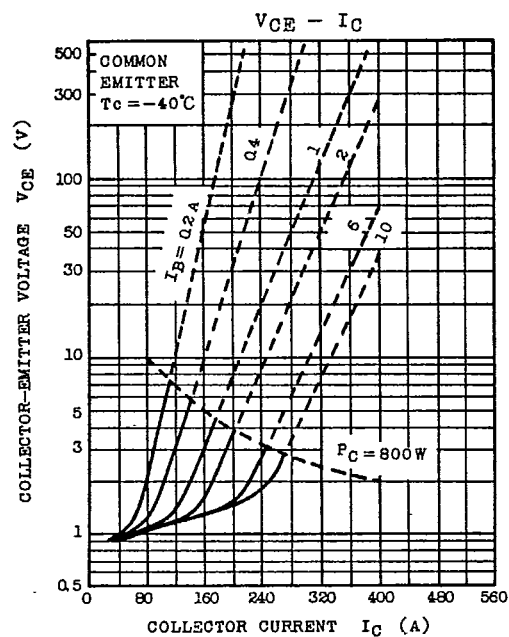
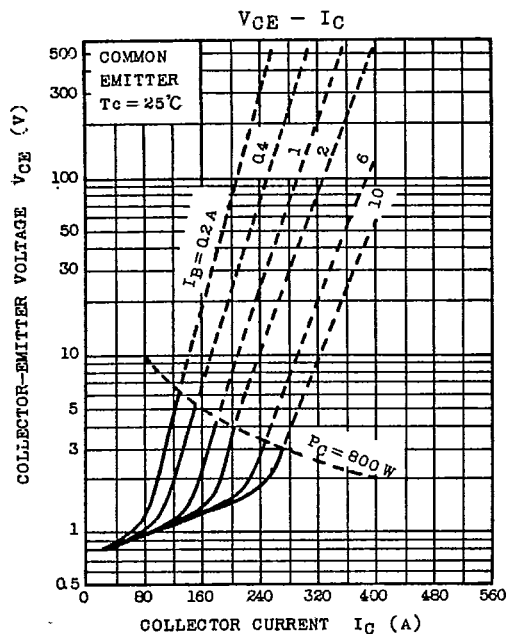
TOSHIBA CORPORATION

GT1A2A



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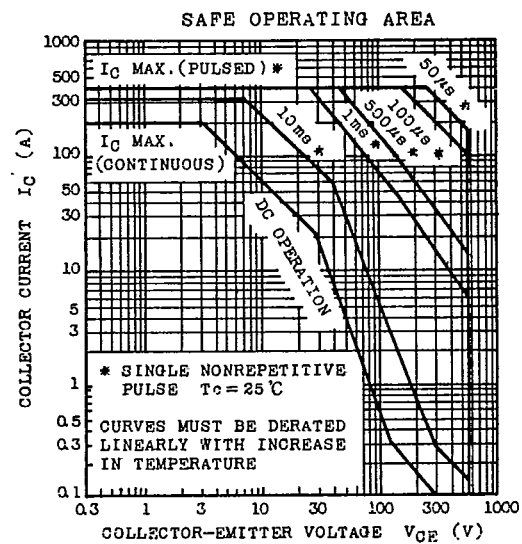
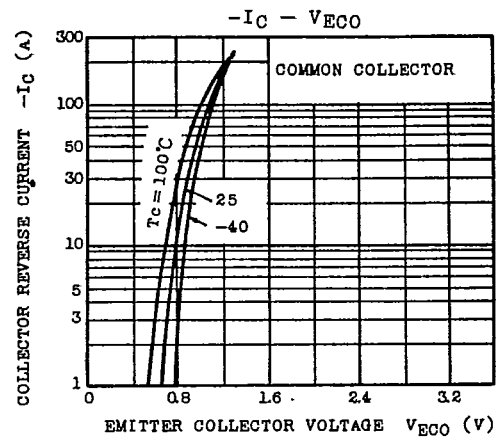
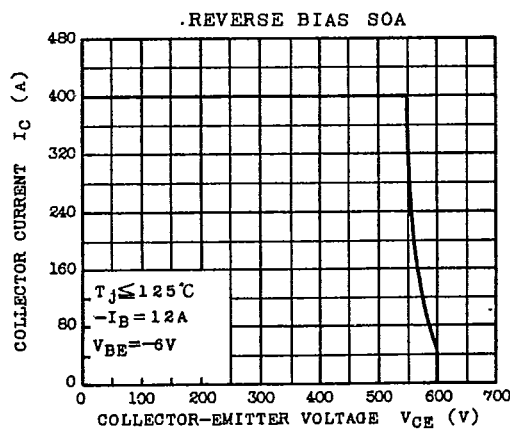
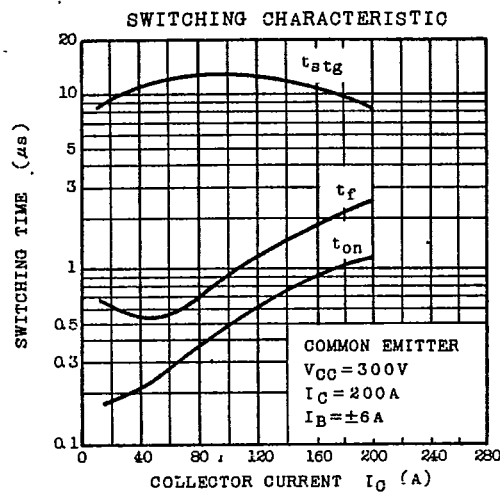
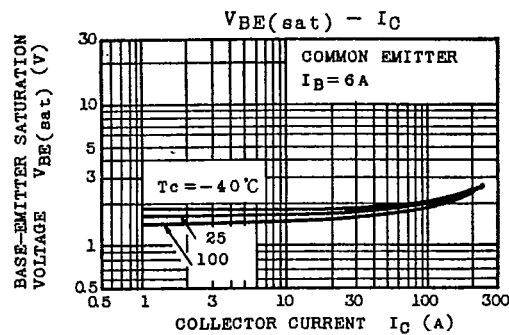
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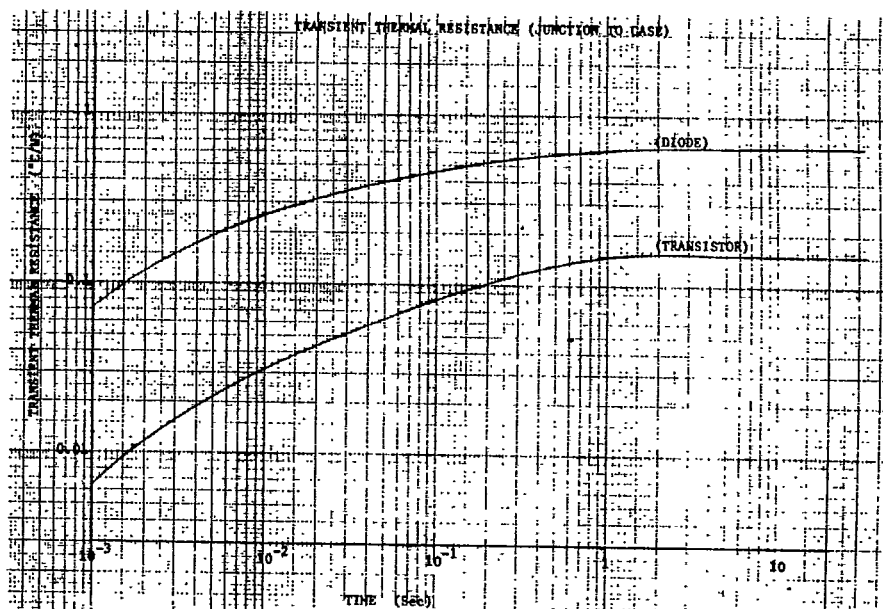
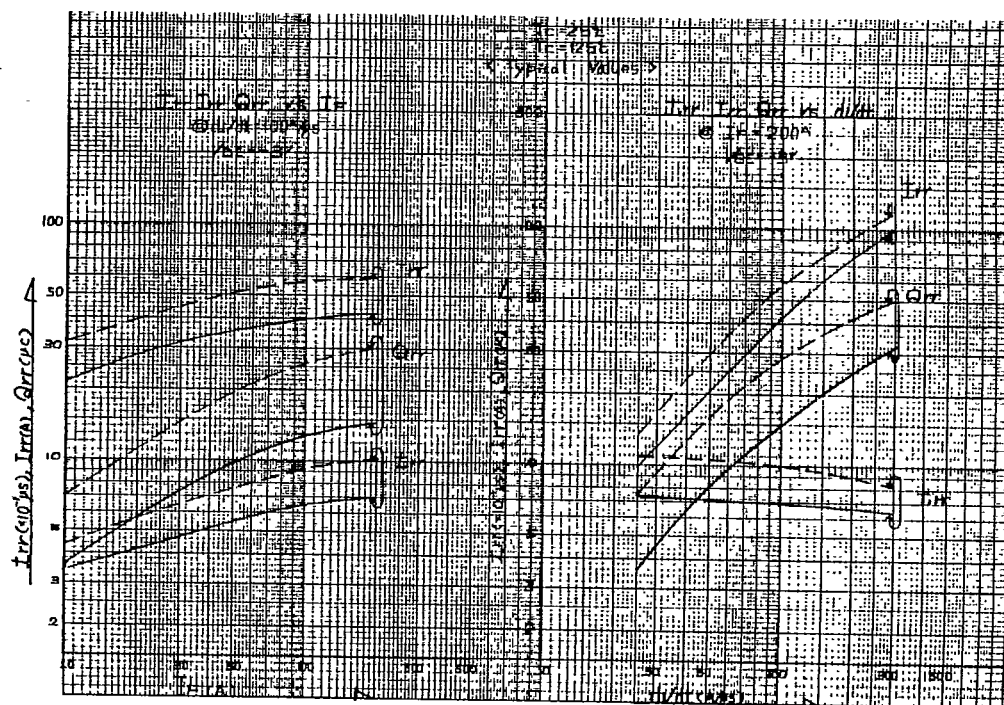
GT1A2



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